


APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	METHOD OF PROGRAMMING A FLASH MEMORY THROUGH BOOSTING A VOLTAGE LEVEL OF A SOURCE LINE		
Application Type : regular, utility Attorney Docket Number : EMEP0061USA			
Correspondence address: Customer Number: 027765			
			
Inventors Information: <u>Inventor 1:</u> Applicant Authority Type: Inventor Citizenship: TW Given Name: Ching-Sung Family Name: Yang Residence: City of Residence: Hsin-Chu City Country of Residence: TW Address-1 of Mailing Address: 8F-1, No. 20, Lane 59, Chien-Kung 1st Rd. Address-2 of Mailing Address: City of Mailing Address: Hsin-Chu City State of Mailing Address: Postal Code of Mailing Address: Country of Mailing Address: TW Phone: Fax: E-mail: <u>Inventor 2:</u> Applicant Authority Type: Inventor Citizenship: TW Given Name: Hsiang-Chung Family Name: Chang Residence: City of Residence: Tai-Chung City			

Country of Residence: TW
Address-1 of Mailing Address: 3F-8, No. 319, Sec. 2, Chang-An Rd., Hsi-Tun
Address-2 of Mailing Address: District
City of Mailing Address: Tai-Chung City
State of Mailing Address:
Postal Code of Mailing Address:
Country of Mailing Address: TW
Phone:
Fax:
E-mail:

Inventor 3:

Applicant Authority Type: Inventor
Citizenship: TW
Given Name: Wei-Zhe
Family Name: Wong
Residence:
City of Residence: Tai-Nan City
Country of Residence: TW
Address-1 of Mailing Address: No.119, Lane 300, Sec.1, Fu-Nung St.
Address-2 of Mailing Address:
City of Mailing Address: Tai-Nan City
State of Mailing Address:
Postal Code of Mailing Address:
Country of Mailing Address: TW
Phone:
Fax:
E-mail:

Attorney Information:

practitioner(s) at Customer Number:

027765



as our attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.